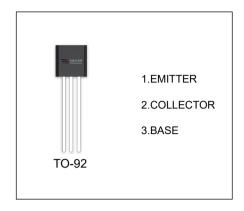


# MPS2222 TRANSISTOR (NPN)

#### **FEATURES**

General Purpose Switching and Amplification



#### **ORDERING INFORMATION**

Part Number	Package	Packing Method	Pack Quantity
MPS2222	TO-92	Bulk	1000pcs/Bag
MPS2222-TA	TO-92	Tape	2000pcs/Box

### MAXIMUM RATINGS (T<sub>a</sub>=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V <sub>CBO</sub>	Collector-Base Voltage	60	V
V <sub>CEO</sub>	Collector-Emitter Voltage	30	V
V <sub>EBO</sub>	Emitter-Base Voltage	5	V
Ic	Collector Current -Continuous	0.6	Α
Pc	Collector Power Dissipation	625	mW
R <sub>θJA</sub>	Thermal Resistance From Junction To Ambient 200		°C/W
T <sub>J</sub> ,T <sub>stg</sub>	Operation Junction and Storage Temperature Range	-55~+150	°C



## $T_a \text{=} 25\, ^{\circ}\text{C}\,$ unless otherwise specified

Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
Collector-base breakdown voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> = 0.01mA,I <sub>E</sub> =0	60			V
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> =10mA,I <sub>B</sub> =0	30			V
Emitter-base breakdown voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> =0.01mA,I <sub>C</sub> =0	5			V
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> =50V,I <sub>E</sub> =0			0.01	μA
Collector cut-off current	ICEX	Vce=60V,Veb(off)=3V			0.01	μA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> =3V,I <sub>C</sub> =0			0.1	μA
DC current gain	h <sub>FE(1)</sub> *	V <sub>CE</sub> =10V, I <sub>C</sub> =150mA	100		300	
	h <sub>FE(2)</sub>	V <sub>CE</sub> =10V, I <sub>C</sub> =0.1mA	35			
	h <sub>FE(3)</sub>	V <sub>CE</sub> =10V, I <sub>C</sub> =500mA	30			
Collector-emitter saturation voltage	V <sub>CE(sat)</sub> *	I <sub>C</sub> =500mA,I <sub>B</sub> =50mA			1	V
Base-emitter saturation voltage	V <sub>BE (sat)</sub> *	I <sub>C</sub> =500mA,I <sub>B</sub> =50mA			2	V
Collector output capacitance	C <sub>ob</sub>	V <sub>CB</sub> =10V,I <sub>E</sub> =0, f=100MHz			8	pF
Transition frequency	f <sub>T</sub>	Vc=20V,lc=20mA, f=100MHz	250			MHz
Delay time	t <sub>d</sub>	Vcc=30V, VBE(off)=-0.5V			10	nS
Rise time	t <sub>r</sub>	Ic=150mA , I <sub>B1</sub> = 15mA			25	nS
Storage time	t <sub>s</sub>	Vcc=30V, Ic=150mA			225	nS
Fall time	t <sub>f</sub>	-   Iв1=Iв2=15mA			60	nS

<sup>\*</sup>Pulse test: pulse width ≤300µs, duty cycle≤ 2.0%.